



Engineering
Standards
Data

MICROWAVE ASSOCIATES, INC.

SEMICONDUCTOR DIVISION

BURLINGTON, MASSACHUSETTS
Western Union FAX-TWX Burlington, Mass., 942-Browning 2-3000

DIFFUSED
SILICON MESA
COMPUTER
DIODES



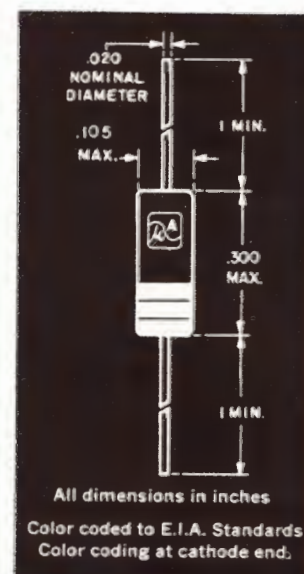
SUBMINIATURE, FAST-SWITCHING, LOW-CAPACITANCE SILICON DIODE

These diodes are designed for use in circuits requiring exceptionally fast recovery time and response. They are hermetically sealed in subminiature glass cases and have gold-plated, copper-clad steel leads that may be easily welded or soldered.

These extremely rugged diodes withstand the most stringent military environments and can be supplied to meet the most severe reliability specifications.

The reverse current characteristics make them an ideal choice in circuits demanding low leakage currents, especially where the accumulated leakage current from many diodes can cause circuit malfunction.

IN 908



MAXIMUM RATINGS @ 25°C

	SYMBOL	MIN	MAX	UNITS
Forward Current Steady-State DC	I_o		100	mAdc
Peak Surge Current (1 sec.)	i surge		250	mAdc
Reverse Voltage Steady-State DC	V_R		40	Vdc
Power Dissipation	P		250	mW
Operating & Storage Temperature Range	T	-65	150	°C
Derating above 25°C (free air)		1.5		mW/°C

ELECTRICAL SPECIFICATIONS @ 25°C

TEST	TEST CONDITIONS	SYMBOL	MIN	MAX	UNITS
Forward Voltage Drop	$I_F = 10.0$ mAdc	V_F		1.0	Vdc
Reverse Current	$V_R = -40$ Vdc $T = 100^\circ\text{C}$	I_R		0.1	μAdc
Capacitance*	$V_R = -6$ Vdc	C_{-6}		10.0	μAdc
Recovery Time	$I_F = 10$ mAdc switched to $V_R = 5.0$ Vdc through 100 ohm loop to 1.0 ma.	t_{rr}		2.5 .004	pf psec.

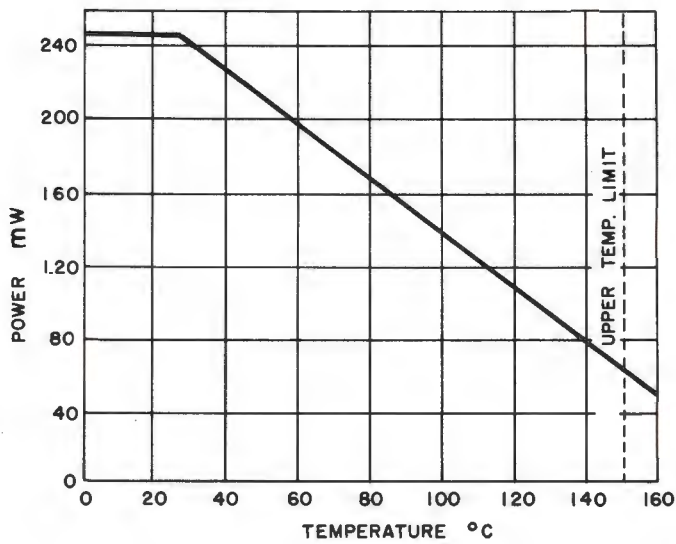
* Average case capacitance is 0.20 pf. Junction capacitance at zero bias is approximately twice that at -6 volts.

These specifications are in accordance with MIL-S-19500B.

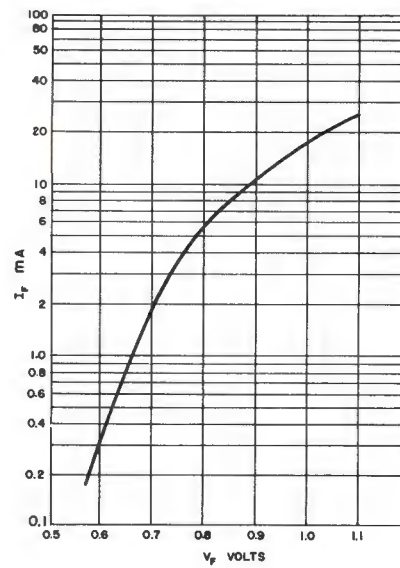
All specifications listed herein are subject to modification.

TYPICAL ELECTRICAL CHARACTERISTICS

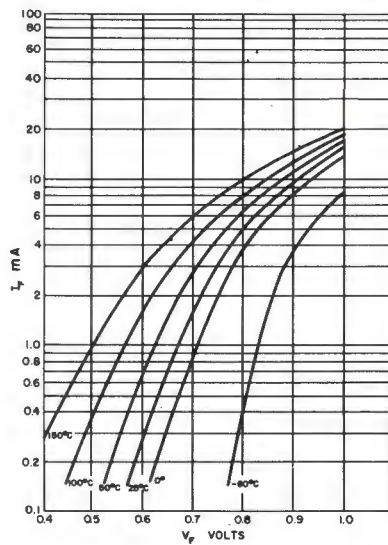
POWER DERATING



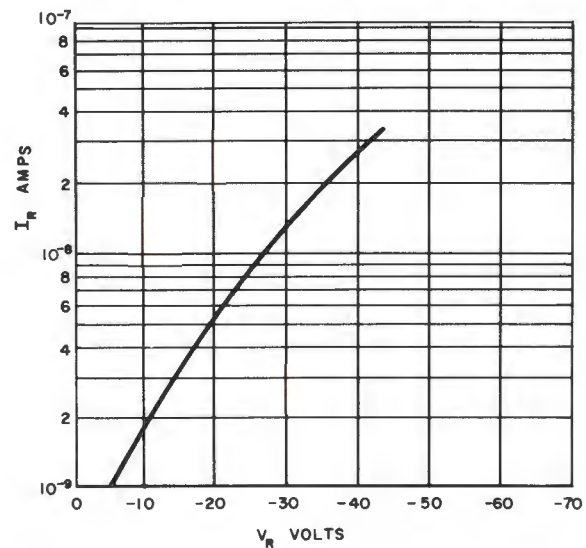
FORWARD CHARACTERISTIC AT 25°C



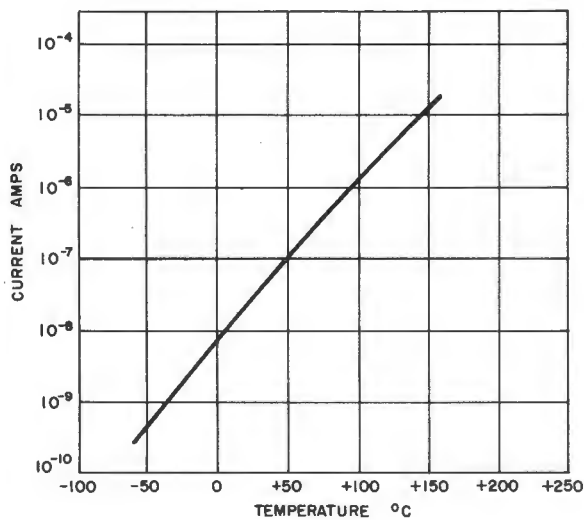
VARIATION OF FORWARD CHARACTERISTIC WITH TEMPERATURE



REVERSE CHARACTERISTIC AT 25°C



VARIATION OF REVERSE CURRENT WITH TEMPERATURE AT -40V



REVERSE RECOVERY TIME TEST CIRCUIT

